Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	147	("20010009784"|"20020074598"|"20020086 472"|"20020086497"|"20020090791"|"2003 0032261"|"20030040158"|"20030057184"|" 20030067035"|"3602841"|"4665415"|"4853 076"|"4855245"|"4952524"|"4958213"|"500 6913"|"5060030"|"5081513"|"5108843"|"51 34085"|"5310446"|"5354695"|"5371399"|"5 391510"|"5459346"|"5471948"|"5557122"|" 5561302"|"5565697"|"5571741"|"5592007"| "5592018"|"5670798"|"5679965"|"5683934 "|"5840593"|"5861651"|"5880040"|"594073 6"|"5946559"|"5960297"|"5989978"|"60081 26"|"6025280"|"6046464"|"6066545"|"6090 684"|"6107143"|"6117722"|"6133071"|"616 5383"|"6221735"|"6228694"|"6246095"|"62 55169"|"6261964"|"6265317"|"6274444"|"6 281532"|"6284623"|"6284626"|"6319794"|" 6361885"|"6362082"|"6368931"|"6403486"| "6403975"|"6406973"|"6461936"|"6476462 "|"6493497"|"6498358"|"6501121"|"650665 2"|"6509618"|"6521964"|"6531369"|"65317 40").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 15:33
L2	35	1 and ((tensile compress$3) near stress)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 15:58
L3	112	1 NOT 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:13
L4	2	("6563152").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	OFF	2005/07/20 16:13
L5	5	("5891793" | "5955745" | "6060387" | "6069046" | "6111292").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/20 16:13
L6	12	("5120668" | "5200352" | "5374574" | "5374575" | "5376578" | "5434093" | "5436482" | "5534447" | "5576574" | "5597752" | "5858848" | "5933738").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/20 16:16
L7	7	("5120668" | "5200352" | "5374574" | "5374575" | "5376578" | "5534447" | "5597752").PN.	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/20 16:28
L8	34034	(recess$2 groove$2 open$3) near2 substrate	US-PGPUB; USPAT; USOCR	OR	ON	2005/07/20 16:30

L9	17	((recess$2 groove$2 open$3) near2 substrate) WITH ((stress near material$1) ((compress$3 tensile) near stress))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:51
L10	969	((recess$2 groove$2 open$3) near2 substrate) AND ((stress near material$1) ((compress$3 tensile) near stress))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:36
L11	33	10 and ((enhanc$3 (electron hole)) near mobility)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:47
L12	246	10 and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:50
L13	4	12 and ((first near (recess$2 groove$2 open$3)) WITH (second near (recess$2 groove$2 open$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:59
L14	3445	(first near (recess$2 groove$2 open$3)) WITH (second near (recess$2 groove$2 open$3)) WITH substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:44
L15	443	14 and (CMOS MOSFET FET)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:46
L16	393	14 and ((CMOS MOSFET FET MOS) WITH gate)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:49
L17	25	16 and ((enhanc$3 (electron hole)) near mobility)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:47

L18	840	14 and (CMOS MOSFET FET MOS (field adj effect adj transistor$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:58
L19	653	18 and gate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:50
L20	12	19 AND ((stress near material$1) ((compress$3 tensile) near stress))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:54
L21	13	18 AND ((stress near material$1) ((compress$3 tensile) near stress))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:55
L22	0	19 AND (mandrel near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:54
L23	1895	(mandrel near (layer film))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:55
L24	0	23 AND 14	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:55
L25	79	23 AND ((stress near material$1) ((compress$3 tensile) near stress))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:58
L26	72335	((stress near material$1) ((compress$3 tensile) near stress))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:58

L27	7202	26 and (CMOS MOSFET FET MOS (field adj effect adj transistor$1))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:58
L28	58	27 AND ((first near (recess$2 groove$2 open$3)) WITH (second near (recess$2 groove$2 open$3)))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT ; IBM_TDB	OR	ON	2005/07/20 16:59